



P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 30	0.053 at V _{GS} = - 10 V	- 4.0		
- 30	0.086 at V _{GS} = - 4.5 V	- 3.1		

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET

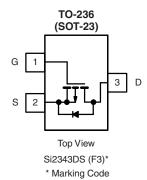
Pb-free Available

RoHS'

HALOGEN
FREE

APPLICATIONS

- Load Switch
- PA Switch



Ordering Information: Si2343DS-T1

Si2343DS-T1-E3 (Lead (Pb)-free)

Si2343DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dusin Comment /T 450 °C\a.b	T _A = 25 °C	I-	- 4.0	- 3.1	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C	- I _D	- 3.2	- 2.5	•
Pulsed Drain Current		I _{DM}	- 15		Α
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 1.0	- 0.6	
Mariana Bana Biratania ah	T _A = 25 °C	P _D	1.25	0.75	W
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	' D	0.8	0.48	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipulation to Applicate	t ≤ 5 s	R _{thJA}	75	100	
Maximum Junction-to-Ambient ^a	Steady State	' ¹thJA	120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zava Cata Valtaga Dvain Current	1	V _{DS} = - 24 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 24 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, $V_{GS} =$ - 10 V	- 15			Α	
D : 0	В	V _{GS} = - 10 V, I _D = - 4.0 A		0.043	0.053	Ω	
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.1 A		0.068	0.086		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.0 A		10		S	
Diode Forward Voltage	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg	V 15 V V 10 V		14	21		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}$ $I_{D} \cong -4.0 \text{ A}$		1.9		nC	
Gate-Drain Charge	Q_{gd}	ID = - 4.0 A		3.7			
Input Capacitance	C _{iss}			540			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		131		pF	
Reverse Transfer Capacitance	C _{rss}			105			
Switching ^c				•			
Turn-On Time	t _{d(on)}	V 45V B 450		10	15		
ium-on time	t _r	V_{DD} = - 15 V, R_L = 15 Ω $I_D \cong$ - 1.0 A, V_{GEN} = - 10 V		15	25		
Turn-Off Time	t _{d(off)}	$R_{G} = 6 \Omega$		31	50	ns	
Turn-Oil Time	t _f	u		20	30		

Notes:

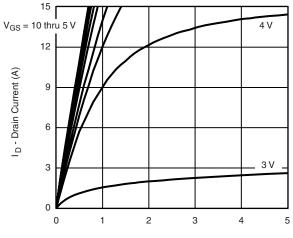
- a. Pulse test: PW $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



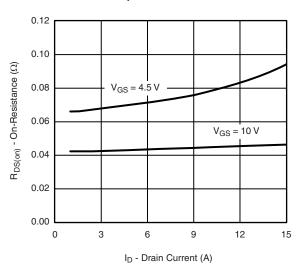


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

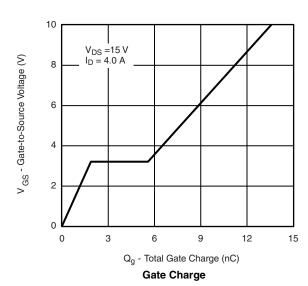


V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

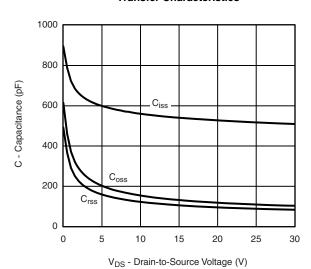


On-Resistance vs. Drain Current

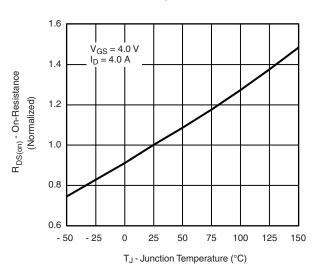


15 12 I_D - Drain Current (A) 9 6 T_C = 125 °C 3 55 °C 0.5 0.0 1.0 1.5 2.0 2.5 3.0 3.5 4.0

V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**



Capacitance

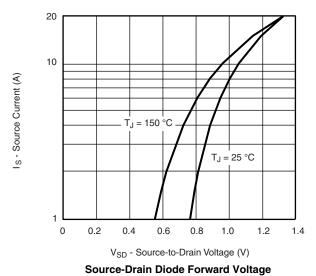


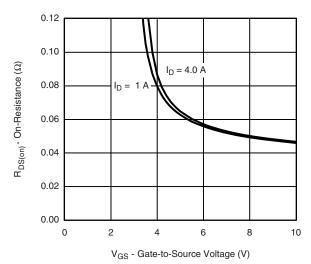
On-Resistance vs. Junction Temperature

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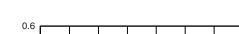
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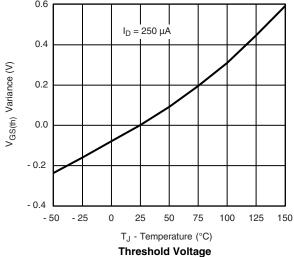
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



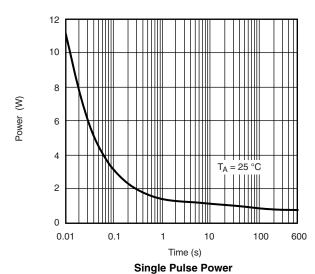


On-Resistance vs. Gate-to-Source Voltage





100



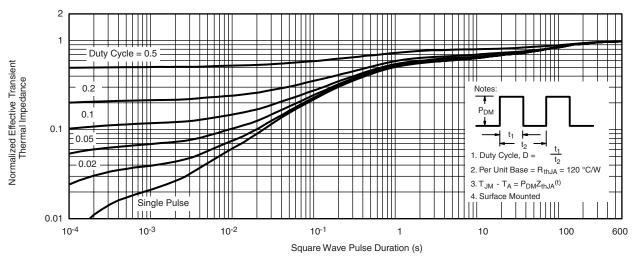
I_{DM} Limited 10 I_D - Drain Current (A) P(t) = 0.0001P(t) = 0.001P(t) = 0.01P(t) = 0.1 $T_A = 25 \, ^{\circ}C$ 0.1 Single Pulse P(t) = 1 **BVDSS Limite** 0.01 0.1 100

 V_{DS} - Drain-to-Source Voltage (V)
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



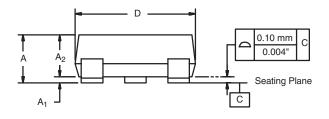
Normalized Thermal Transient Impedance, Junction-to-Ambient

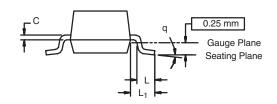
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SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

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